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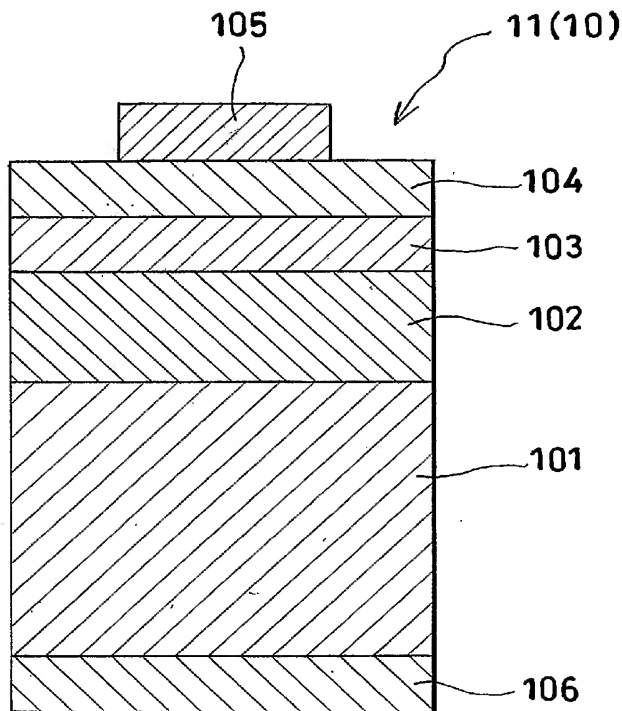
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(54) Title: BORON PHOSPHIDE-BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE



(57) Abstract: A boron phosphide-based semiconductor light-emitting device includes a substrate of silicon single crystal, a first cubic boron phosphide-based semiconductor layer that is provided on a surface of the substrate and contains twins, a light-emitting layer that is composed of a hexagonal Group III nitride semiconductor and provided on the first cubic boron phosphide-based semiconductor layer and a second cubic boron phosphide-based semiconductor layer that is provided on the light-emitting layer, contains twins and has a conduction type different from that of the first cubic boron phosphide-based semiconductor layer.

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